

# NPN SILICON GERMANIUM RF TRANSISTOR NESG3031M14

### NPN SiGe RF TRANSISTOR FOR LOW NOISE, HIGH-GAIN AMPLIFICATION 4-PIN LEAD-LESS MINIMOLD (M14, 1208 PKG)

#### FEATURES

- The device is an ideal choice for low noise, high-gain amplification
- ★ NF = 0.6 dB TYP.,  $G_a = 16.0$  dB TYP. @  $V_{CE} = 2$  V,  $I_c = 6$  mA,  $f = 2.4$  GHz  
NF = 0.95 dB TYP.,  $G_a = 10.0$  dB TYP. @  $V_{CE} = 2$  V,  $I_c = 6$  mA,  $f = 5.2$  GHz  
NF = 1.1 dB TYP.,  $G_a = 9.5$  dB TYP. @  $V_{CE} = 2$  V,  $I_c = 6$  mA,  $f = 5.8$  GHz
- Maximum stable power gain: MSG = 15.0 dB TYP. @  $V_{CE} = 3$  V,  $I_c = 20$  mA,  $f = 5.8$  GHz
- SiGe HBT technology (UHS3) adopted:  $f_{max} = 110$  GHz
- 4-pin lead-less minimold (M14, 1208 PKG)

#### ★ ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG3031M14	NESG3031M14-A	4-pin lead-less minimold (M14, 1208 PKG) (Pb-Free) <sup>Note</sup>	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 1 (Collector), Pin 4 (Emitter) face the perforation side of the tape
NESG3031M14-T3	NESG3031M14-T3-A		10 kpcs/reel	

**Note** With regards to terminal solder (the solder contains lead) plated products (conventionally plated), contact your nearby sales office.

**Remark** To order evaluation samples, contact your nearby sales office.  
Unit sample quantity is 50 pcs.

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	$V_{CBO}$	12.0	V
Collector to Emitter Voltage	$V_{CEO}$	4.3	V
Emitter to Base Voltage	$V_{EBO}$	1.5	V
Collector Current	$I_c$	35	mA
Total Power Dissipation	$P_{tot}$ <sup>Note</sup>	150	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$

**Note** Mounted on  $1.08 \text{ cm}^2 \times 1.0 \text{ mm}$  (t) glass epoxy PWB

**Caution** Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0 mA	–	–	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0 mA	–	–	100	nA
DC Current Gain	h <sub>FE</sub> <sup>Note 1</sup>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA	220	300	380	–
RF Characteristics						
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 20 mA, f = 5.8 GHz	6.5	9.0	–	dB
★ Noise Figure (1)	NF	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 2.4 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	0.6	–	dB
Noise Figure (2)	NF	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.2 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	0.95	–	dB
Noise Figure (3)	NF	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	1.1	1.5	dB
★ Associated Gain (1)	G <sub>a</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 2.4 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	16.0	–	dB
Associated Gain (2)	G <sub>a</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.2 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	10.0	–	dB
Associated Gain (3)	G <sub>a</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	7.5	9.5	–	dB
Reverse Transfer Capacitance	C <sub>re</sub> <sup>Note 2</sup>	V <sub>CB</sub> = 2 V, I <sub>E</sub> = 0 mA, f = 1 MHz	–	0.15	0.25	pF
Maximum Stable Power Gain	MSG <sup>Note 3</sup>	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 20 mA, f = 5.8 GHz	12.0	15.0	–	dB
Gain 1 dB Compression Output Power	P <sub>O</sub> (1 dB)	V <sub>CE</sub> = 3 V, I <sub>C (set)</sub> = 20 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	13.0	–	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP <sub>3</sub>	V <sub>CE</sub> = 3 V, I <sub>C (set)</sub> = 20 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	18.0	–	dBm

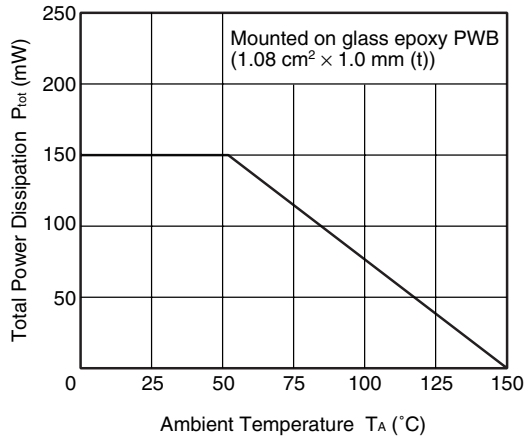
- Notes 1.** Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
- 2.** Collector to base capacitance when the emitter grounded
- 3.**  $MSG = \left| \frac{S_{21}}{S_{12}} \right|$

**h<sub>FE</sub> CLASSIFICATION**

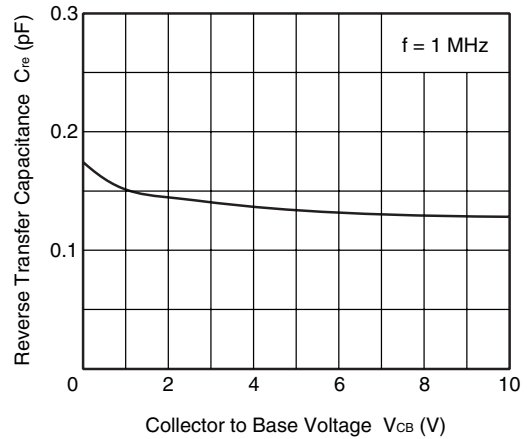
Rank	FB
Marking	zJ
h <sub>FE</sub> Value	220 to 380

TYPICAL CHARACTERISTICS (T<sub>A</sub> = +25°C, unless otherwise specified)

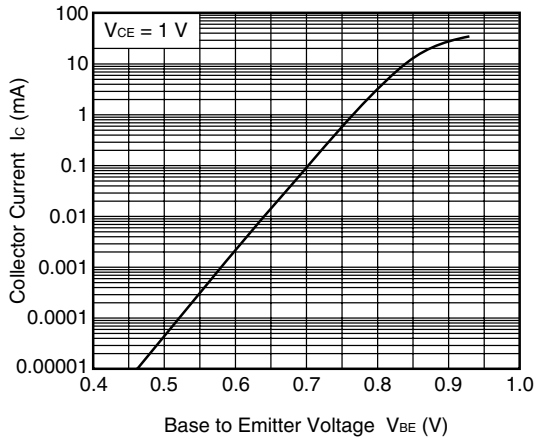
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



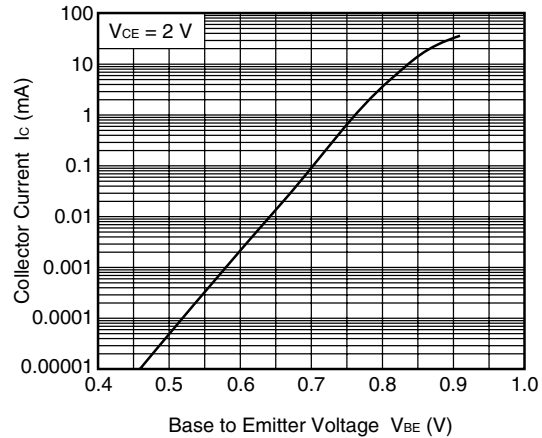
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



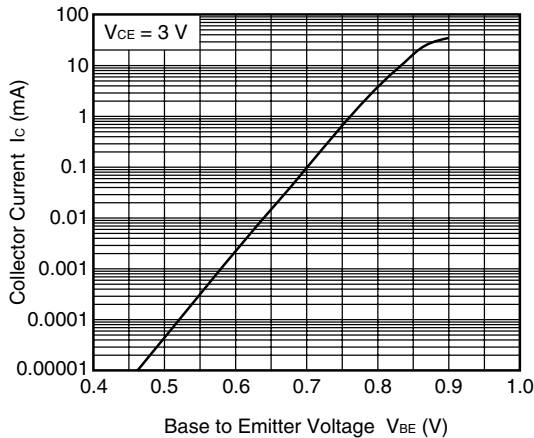
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



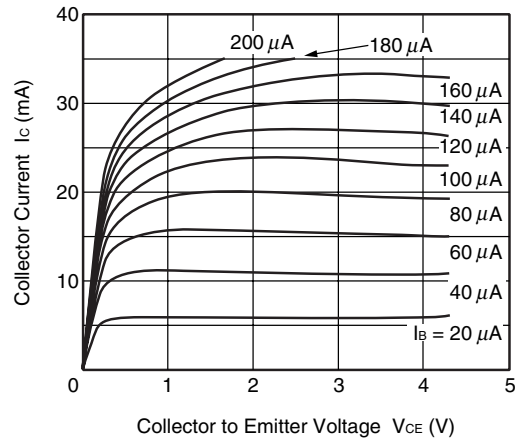
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

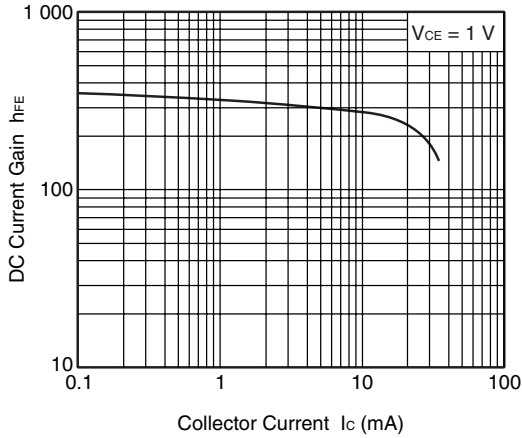


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

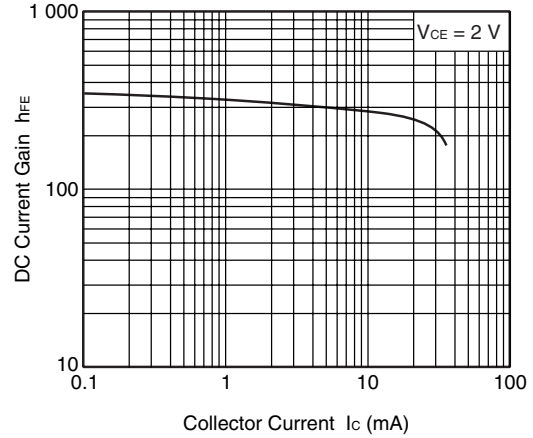


**Remark** The graphs indicate nominal characteristics.

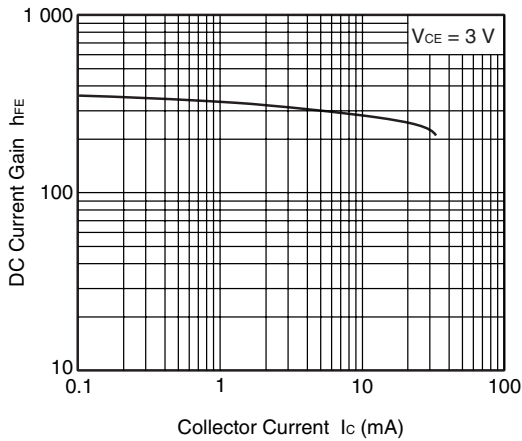
DC CURRENT GAIN vs. COLLECTOR CURRENT



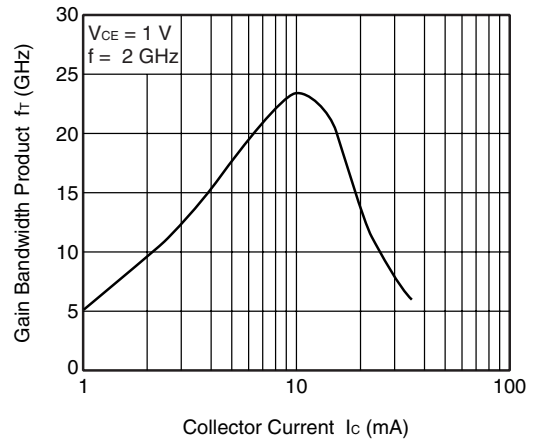
DC CURRENT GAIN vs. COLLECTOR CURRENT



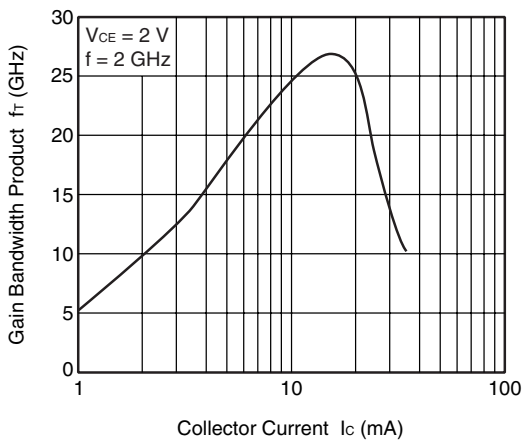
DC CURRENT GAIN vs. COLLECTOR CURRENT



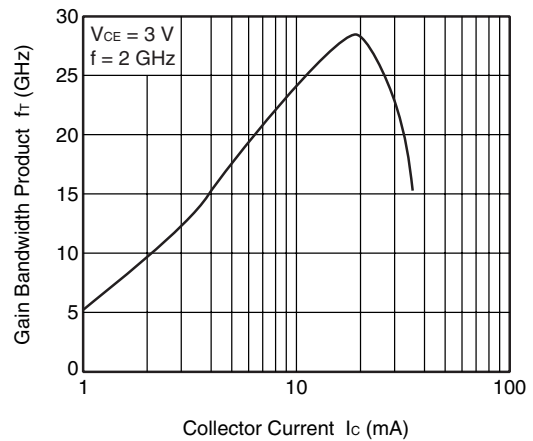
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

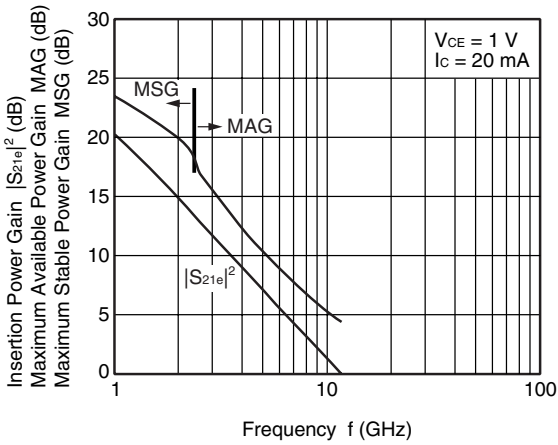


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

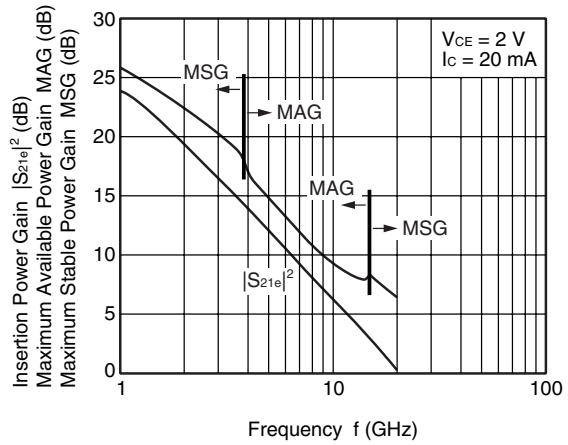


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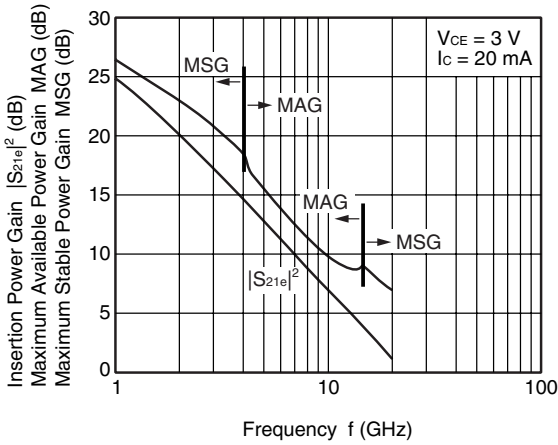
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



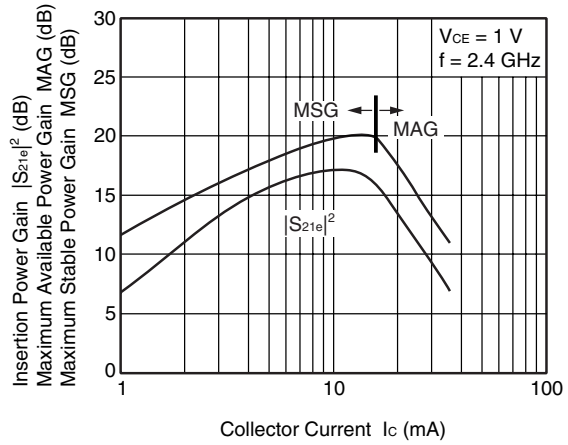
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



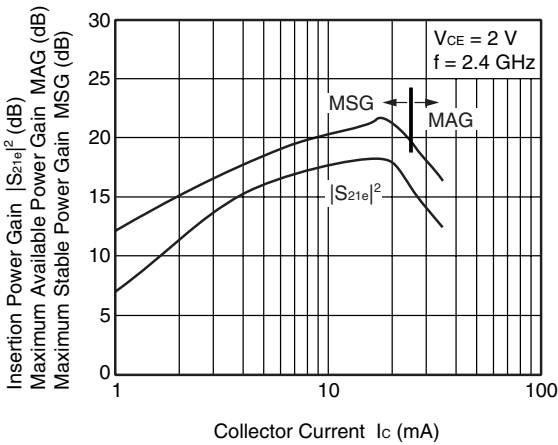
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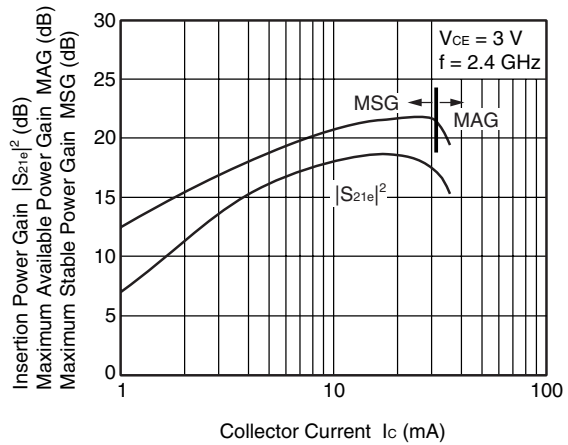
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



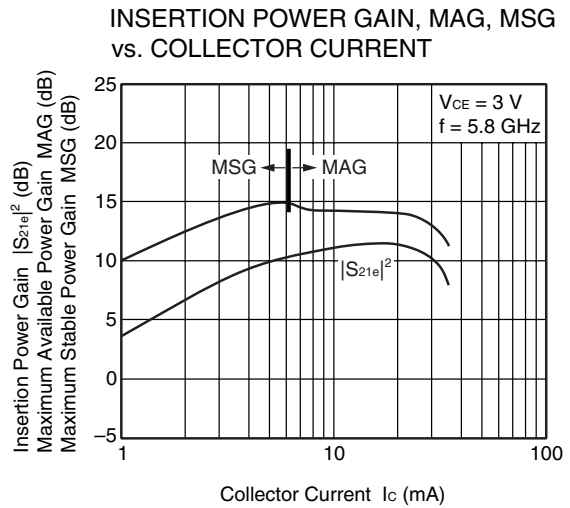
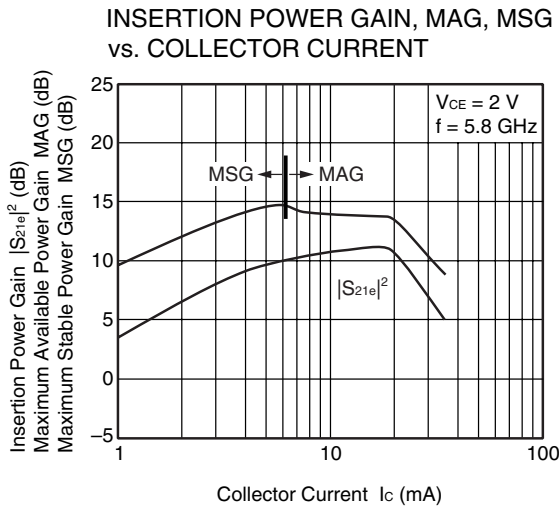
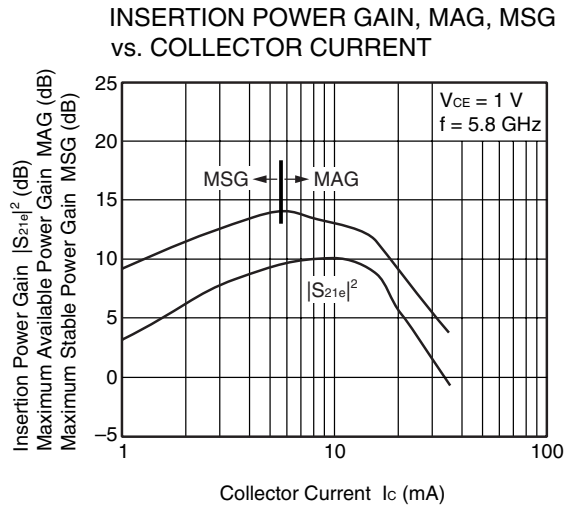
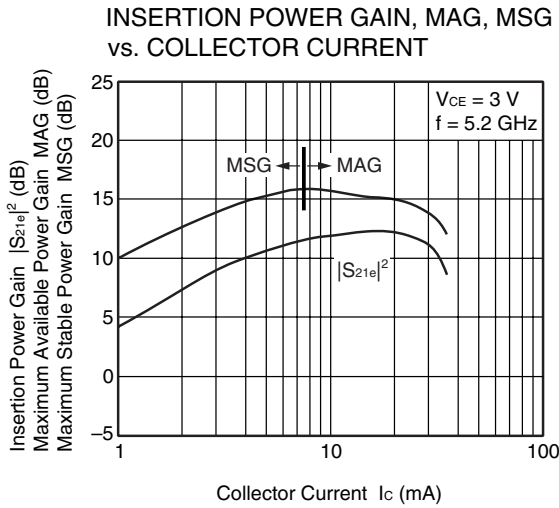
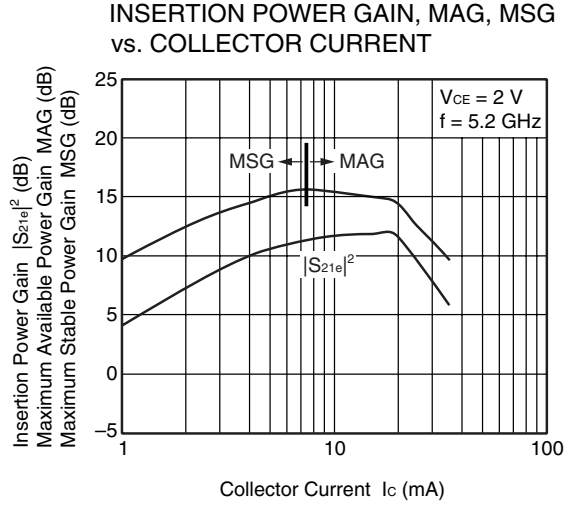
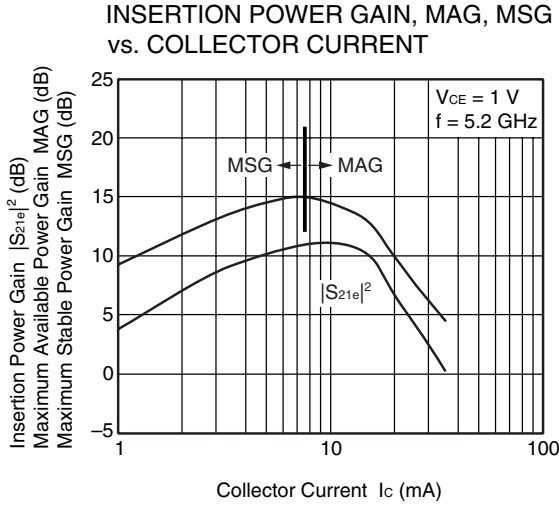
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



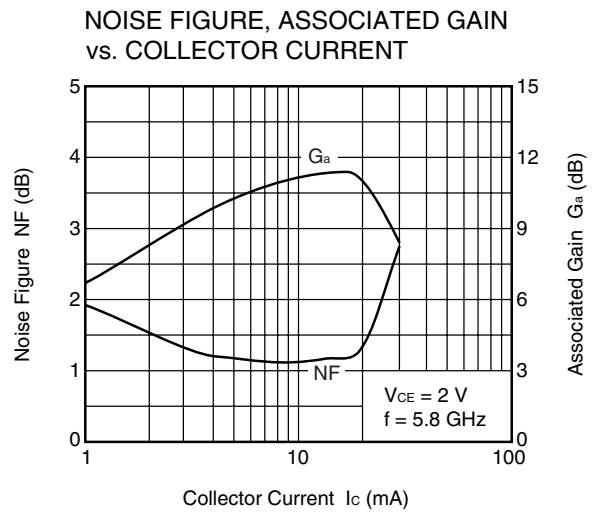
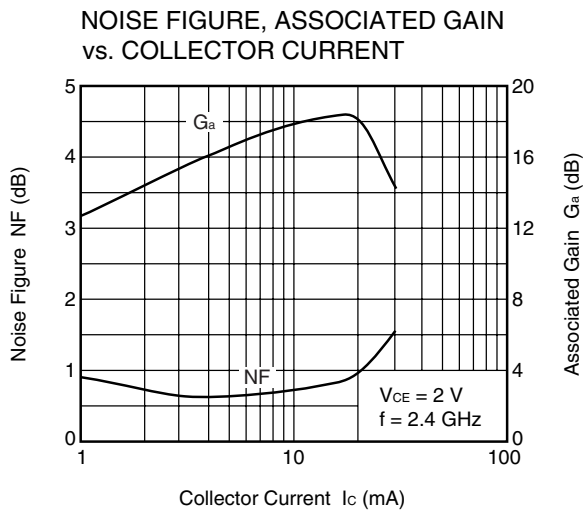
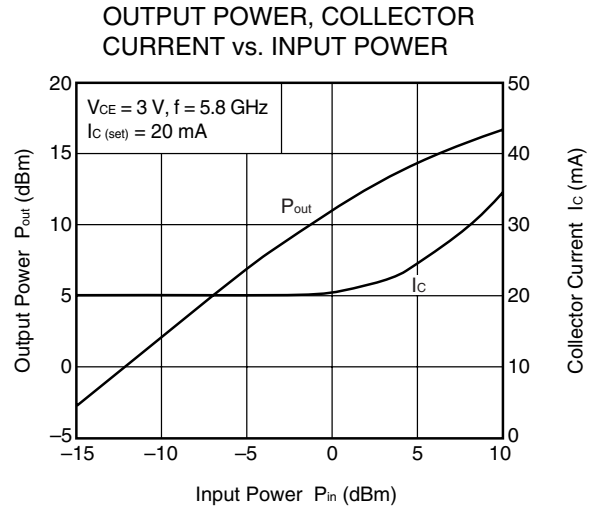
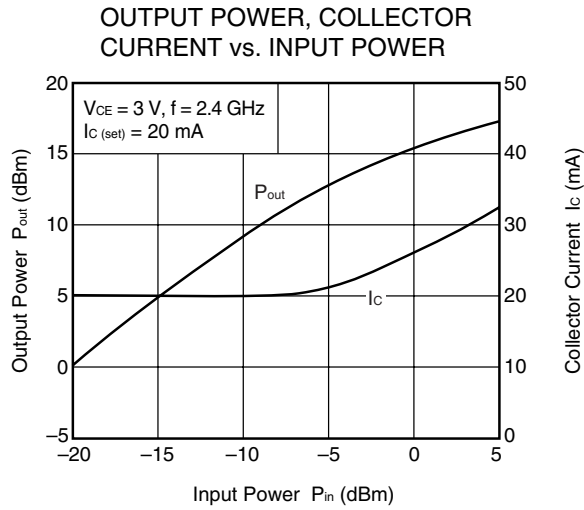
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



**Remark** The graphs indicate nominal characteristics.



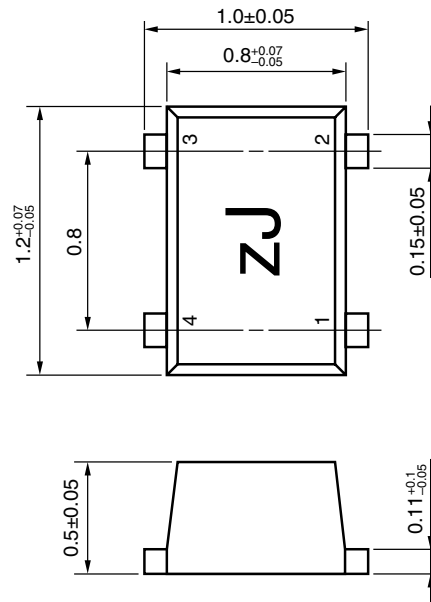
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PACKAGE DIMENSIONS

4-PIN LEAD-LESS MINIMOLD (M14, 1208 PKG) (UNIT: mm)



PIN CONNECTIONS

- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter



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